

IN THE CLAIMS

Please cancel Claims 1-24, 30-32, and 40-58.

1-24. (Cancelled).

25. (Original) A method for manufacturing a semiconductor film comprising the steps of:

preparing a first member including a semiconductor substrate, a semiconductor layer whose resistivity is higher than a resistivity of the semiconductor substrate, and a separation layer provided between the semiconductor substrate and the semiconductor layer; and

separating the semiconductor layer from the semiconductor substrate at the separation layer by heating the first member by induction heating.

26. (Original) A method according to Claim 25, further comprising a step of bonding or attracting a second member which is hardly heated by induction heating, onto the semiconductor layer of the first member, before heating the first member by induction heating.

27. (Original) A method according to Claim 25, further comprising a step of bonding or attracting a second member whose resistivity is higher than a resistivity of the first member, onto the semiconductor layer of the first member, before heating the first member by induction heating.

28. (Original) A method according to Claim 25, wherein the resistivity of the semiconductor layer is at least 10 times the resistivity of the semiconductor substrate.

29. (Original) A method according to Claim 25, wherein the resistivity of the semiconductor layer is at least $1\ \Omega \cdot \text{cm}$, and the resistivity of the semiconductor substrate is equal to or less than $0.1\ \Omega \cdot \text{cm}$.

30-32. (Cancelled).

33. (Original) A method according to Claim 25, wherein said step of heating the semiconductor substrate by induction heating comprises a step of mounting the first member on an induction-heating mount around which a coil is wound, and causing a current to flow in the semiconductor substrate by supplying the coil with a high-frequency current.

34. (Original) A method according to Claim 25, further comprising a step of forming slits in the separation layer before heating the first member by induction heating.

35. (Original) A method according to Claim 25, wherein, in said step of heating the first member by induction heating, a tensile force, a compressive force or a shearing force is simultaneously applied to the separation layer.

36. (Original) A method according to Claim 25, wherein, in said step of heating the first member by induction heating, a pressure or a hydrostatic pressure by a fluid is simultaneously applied to the separation layer.

37. (Original) A method according to Claim 25, further comprising a step of removing a residue of the separation layer remaining on the semiconductor layer according to etching, after separating the semiconductor layer.

38. (Original) A method according to Claim 25, further comprising a step of reutilizing a remaining semiconductor substrate for preparing another first member, after separating the semiconductor layer.

39. (Original) A method according to Claim 38, further comprising a step of removing a residue of the separation layer remaining on the semiconductor substrate according to etching, before reutilizing the semiconductor substrate.

40-58. (Cancelled).